CORRECTION

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Correction: Simulation of the resistance switching performance and synaptic behavior of TiO$_2$-based RRAM devices with CoFe$_2$O$_4$ insertion layers

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Correction for 'Simulation of the resistance switching performance and synaptic behavior of TiO$_2$-based RRAM devices with CoFe$_2$O$_4$ insertion layers' by Fei Yang *et al.*, *Nanoscale*, 2024, **16**, 6729–6738, https://doi.org/10.1039/D3NR05935A.

The authors regret that in the original article, eqn (6), (7), (9) and (10) in section 2.1 were given incorrectly. The correct versions of equations (6), (7), (9) and (10) are shown below.

$$\frac{\partial n_{\mathrm{D}}}{\partial t} = -\nabla \cdot j + G - R = \nabla \cdot (D\nabla n_{\mathrm{D}} - v n_{\mathrm{D}}) + G - R \tag{6}$$

$$\nabla \cdot \sigma \nabla \psi = 0 \tag{7}$$

$$\rho C_{\mathrm{p}} \frac{\partial T}{\partial t} - \nabla \cdot K_{\mathrm{th}} \nabla T = Q = J \cdot E = \sigma |\nabla \psi|^2 \tag{9}$$

$$-\nabla \cdot K_{\mathrm{th}} \nabla T = \sigma |\nabla \psi|^2 \tag{10}$$

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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